SHANGHAI SUNRISE ELECTRONICS CO., LTD. RS1A THRU RS1M SURFACE MOUNT FAST SWITCHING RECTIFIER

## TECHNICAL SPECIFICATION

## VOLTAGE: 50 TO 1000V CURRENT: 1.0A

## FEATURES

- Ideal for surface mount pick and place application
- Low profile package
- Built-in strain relief
- High surge capability
- Glass passivated chip
- Fast recovery for high efficiency
- High temperature soldering guaranteed:
$260^{\circ} \mathrm{C} / 10 \mathrm{sec} /$ at terminal
MECHANICAL DATA
- Terminal: Plated leads solderable per MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O recognized flame retardant epoxy
- Polarity: Color band denotes cathode



## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60 Hz , resistive or inductive load rating at $25^{\circ} \mathrm{C}$, unless otherwise stated,for capacitive load, derate current by 20\%)

| RATINGS | SYMBOL | $\begin{array}{\|l\|} \hline \text { RS } \\ \text { 1A } \\ \hline \end{array}$ | $\begin{aligned} & \mathrm{RS} \\ & \mathrm{1B} \\ & \hline \end{aligned}$ | $\begin{aligned} & \mathrm{RS} \\ & 1 \mathrm{D} \\ & \hline \end{aligned}$ | $\begin{aligned} & \hline \mathrm{RS} \\ & \text { 1G } \\ & \hline \end{aligned}$ | $\begin{aligned} & \hline \mathrm{RS} \\ & 1 \mathrm{~J} \\ & \hline \end{aligned}$ | $\begin{array}{\|l\|} \hline \mathrm{RS} \\ 1 \mathrm{~K} \\ \hline \end{array}$ | $\begin{aligned} & \mathrm{RS} \\ & \mathbf{1 M} \\ & \hline \end{aligned}$ | UNITS |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Maximum Repetitive Peak Reverse Voltage | $\mathrm{V}_{\text {RRM }}$ | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| Maximum RMS Voltage | $\mathrm{V}_{\text {RMS }}$ | 35 | 70 | 140 | 280 | 420 | 560 | 700 | V |
| Maximum DC Blocking Voltage | $V_{D C}$ | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| Maximum Average Forward Rectified Current $\left(\mathrm{T}_{\mathrm{L}}=110^{\circ} \mathrm{C}\right)$ | $\mathrm{I}_{\text {(AV) }}$ |  |  |  | 1.0 |  |  |  | A |
| Peak Forward Surge Current ( 8.3 ms single half sine-wave superimposed on rated load) | $I_{\text {FSM }}$ |  |  |  | 30 |  |  |  | A |
| Maximum Instantaneous Forward Voltage (at rated forward current) | $V_{F}$ |  |  |  | 1.3 |  |  |  | V |
| Maximum DC Reverse Current $\mathrm{T}_{\mathrm{a}}=25^{\circ}$ <br> (at rated DC blocking voltage) $\mathrm{T}_{\mathrm{a}}=125^{\circ}$ <br> Maxim  | $L_{R}$ |  |  |  | $\begin{aligned} & \hline 5.0 \\ & 200 \\ & \hline \end{aligned}$ |  |  |  | $\begin{aligned} & \hline \mu \mathrm{A} \\ & \mu \mathrm{~A} \end{aligned}$ |
| Maximum Reverse Recovery Tim $\epsilon$ (Note 1) | trr |  |  |  |  | 250 |  | 00 | nS |
| Typical Junction Capacitance (Note 2) | $\mathrm{C}_{J}$ |  |  |  | 15 |  |  |  | pF |
| Typical Thermal Resistance (Note 3) | $\mathrm{R}_{\theta}(\mathrm{ja})$ |  |  |  | 30 |  |  |  | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Storage and Operation Junction Temperature | $\mathrm{T}_{\text {STG }}, \mathrm{T}_{J}$ |  |  |  | to +1 |  |  |  | ${ }^{\circ} \mathrm{C}$ |
| 1. Reverse recovery condition $\mathrm{I}_{\mathrm{F}}=0.5 \mathrm{~A}, \mathrm{I}_{\mathrm{R}}=1.0 \mathrm{~A}, \mathrm{Ir}=0.25 \mathrm{~A}$. <br> 2. Measured at 1.0 MHz and applied voltage of $4.0 \mathrm{~V}_{\mathrm{dc}}$ |  |  |  |  |  |  |  |  |  |

